

Silicon PNP Power Transistors

2SB1640

DESCRIPTION

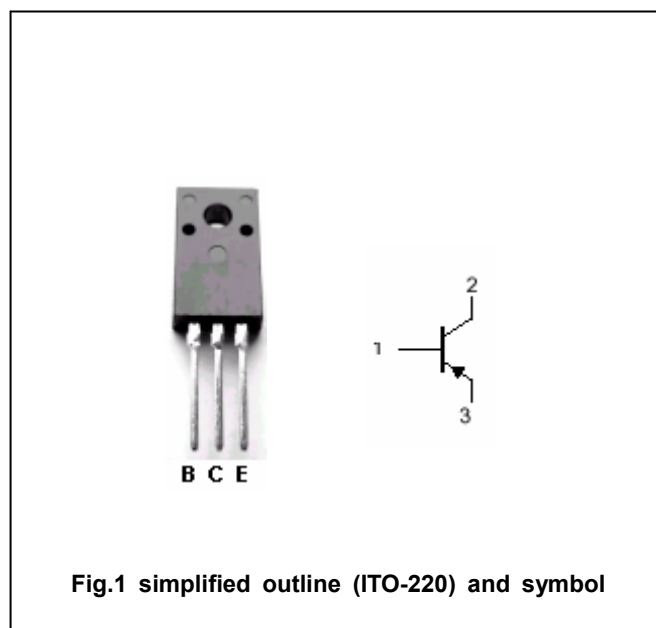
- With ITO-220 package
- Low collector saturation voltage
- Complement to type 2SD2525

APPLICATIONS

- Audio frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-3	A
I_B	Base current		-0.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	1.8	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

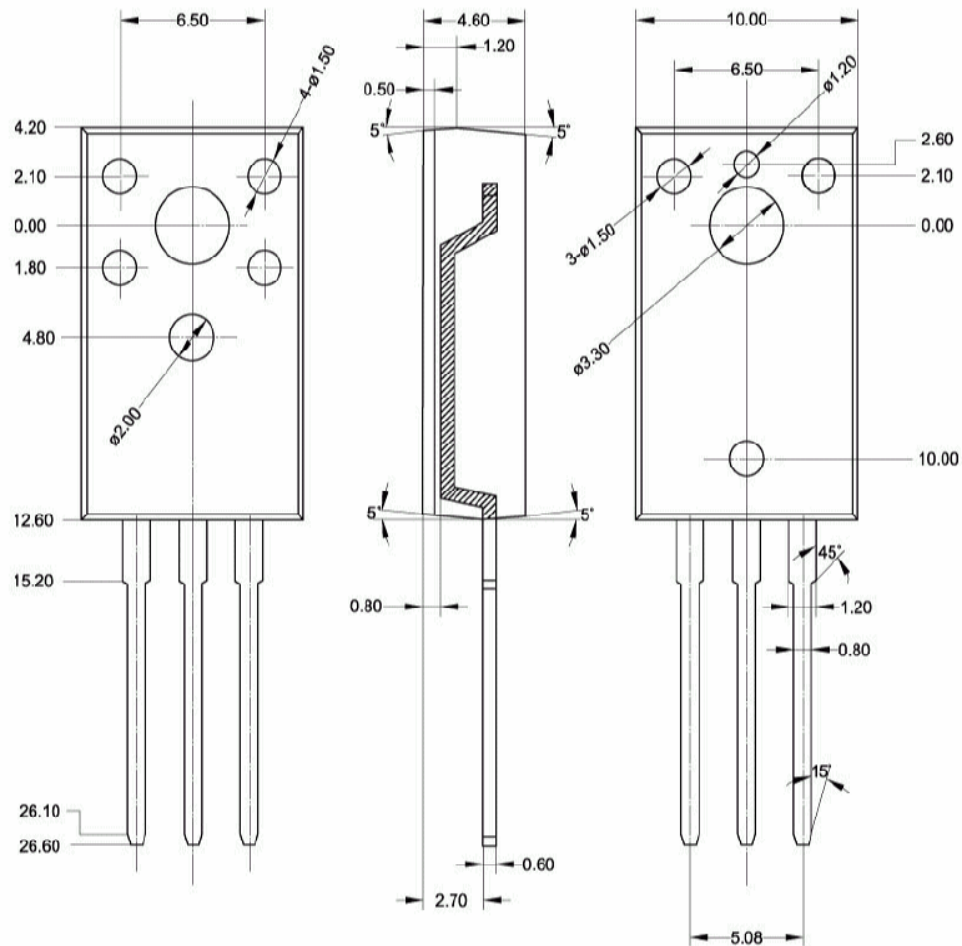
Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA ; I_B=0$	-60			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2A ; I_B=-0.2A$		-1.0	-1.5	V
V_{BE}	Base-emitter on voltage	$I_C=-0.5A ; V_{CE}=-5V$		-0.75	-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-60V ; I_E=0$			-10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-7V ; I_C=0$			-10	μA
h_{FE-1}	DC current gain	$I_C=-0.5A ; V_{CE}=-5V$	100		320	
h_{FE-2}	DC current gain	$I_C=-2A ; V_{CE}=-5V$	15			
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-5V$		9		MHz
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=-10V ; f=1MHz$		50		pF

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.20 mm)